



GP2M020A050H Information



For Reference Only

Part Number GP2M020A050H

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 18A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GP2M020A050H Specifications

Manufacturer Part Number GP2M020A050H Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-220-3 Series TO-220-3 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature	Manufacturer Part Number	GP2M020A050H
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FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature N-Channel 18A (Tc) 1	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2880pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs300 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)	Series	-
Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $10V$ $Vgs(th)$ (Max) @ Id $5V$ @ 250μ AGate Charge (Qg) (Max) @ Vgs $44n$ C @ $10V$ Input Capacitance (Ciss) (Max) @ Vds $2880p$ F @ $25V$ Vgs (Max) $\pm 30V$ FET Feature-Power Dissipation (Max) $290W$ (Tc)Rds On (Max) @ Id, Vgs 300 mOhm @ $9A$, $10V$ Operating Temperature -55 °C ~ 150 °C (TJ)	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	18A (Tc)
Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 2880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) $\pm 30 \text{V}$ FET Feature-Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs $300 \text{ mOhm @ 9A, 10V}$ Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C (TJ)}$	Gate Charge (Qg) (Max) @ Vgs	44nC @ 10V
FET Feature - Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	2880pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 300 mOhm @ 9A, 10V Operating Temperature -55°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	290W (Tc)
	Rds On (Max) @ Id, Vgs	300 mOhm @ 9A, 10V
Mounting Type Through Hole	Operating Temperature	-55°C ~ 150°C (TJ)
Thought true	Mounting Type	Through Hole
Supplier Device Package TO-220	Supplier Device Package	TO-220
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

GP2M020A050H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP2M020A050H Payment Methods



















GP2M020A050H Shipping Methods













If you have any question about GP2M020A050H, please do not hesitate to contact us!

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